

Low-Cost Diode Arrays for Production-Scale Fusion Energy Installations

HECDPSSL
September 12, 2012

Northrop Grumman Cutting Edge Optronics

Ryan Feeler, Ph.D., Jeremy Junghans, Joe Levy

Outline



- Disclaimers...
- NGCEO Overview
- Diode Specifications – LIFE and similar programs
- Potential Diode Package
- What about VCSELs?
- Outlook

Disclaimers...

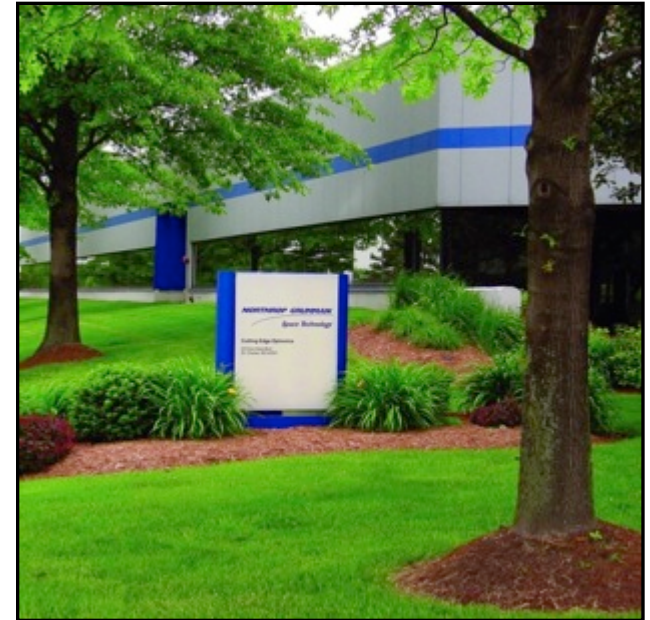


-
- Vantage point – diode lasers
 - Most of my information is based on U.S. / LIFE
 - Suggested design is just one of many options

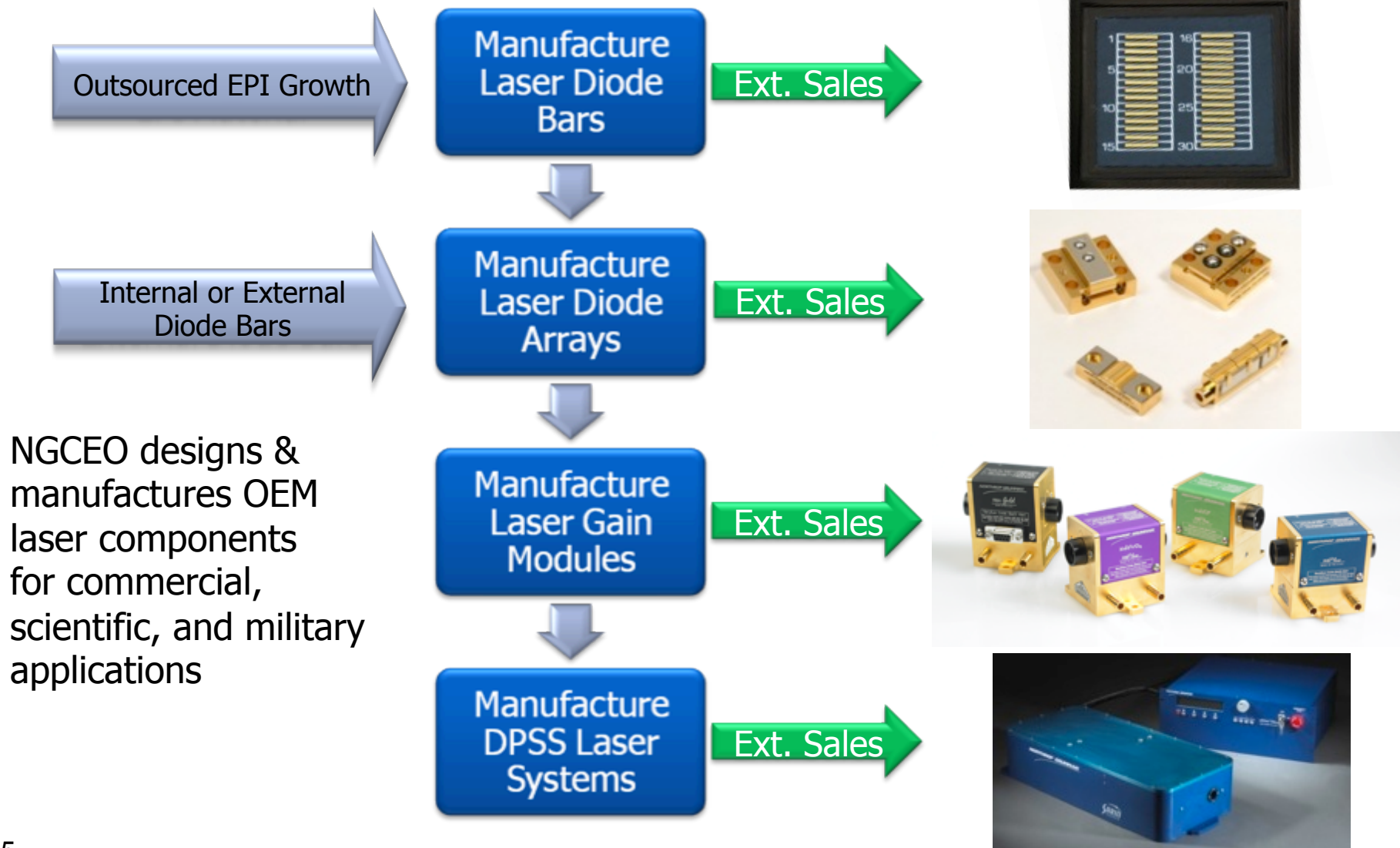
NGCEO Overview



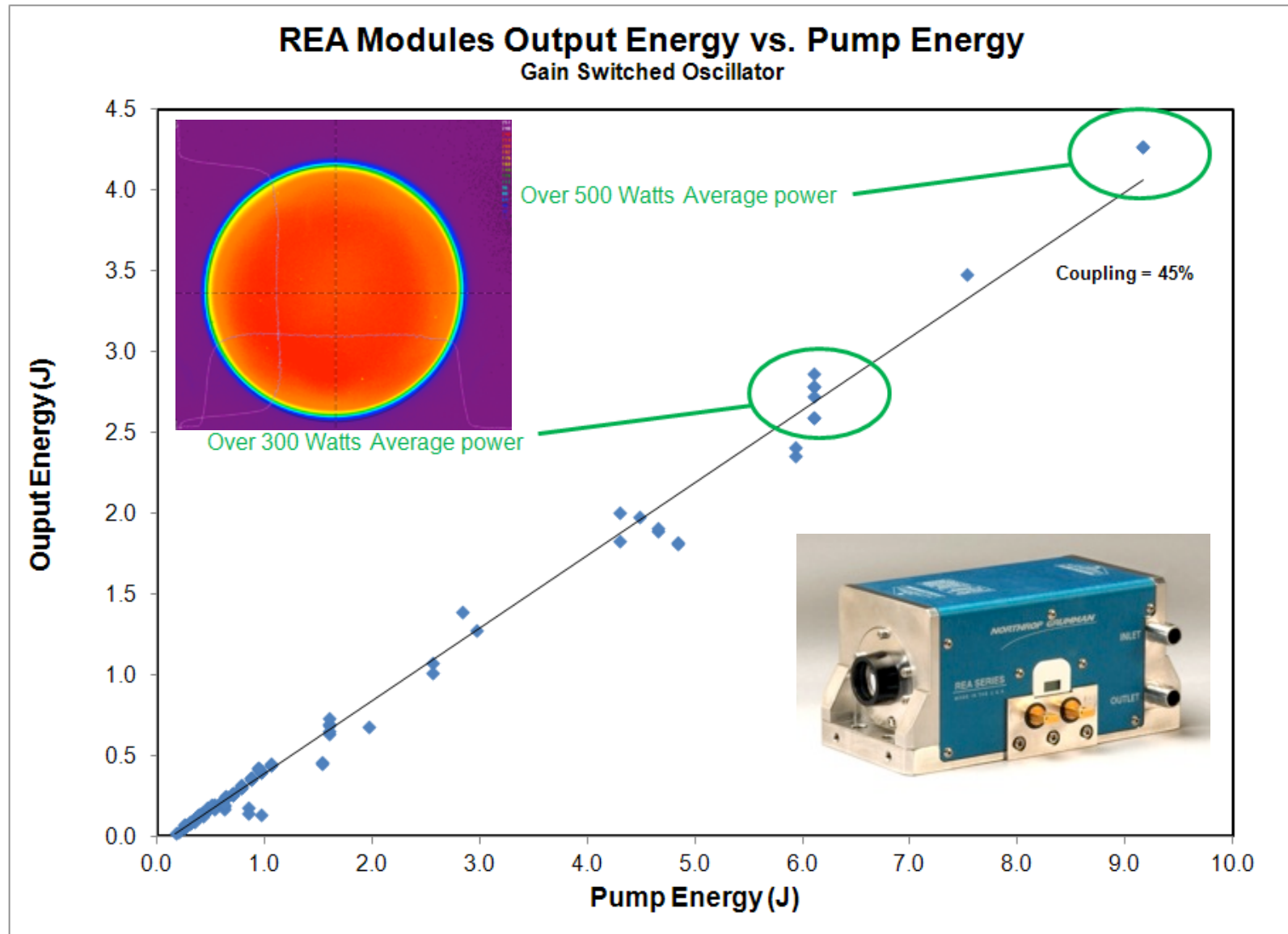
- Cutting Edge Optronics is a wholly-owned subsidiary of Northrop Grumman
- Located outside of St. Louis, MO
 - 36,000 ft² facility, ~ 90 people
 - All manufacturing and R&D is done at this facility
 - Bar fabrication and packaging since late 1990s



NGCEO Product Overview



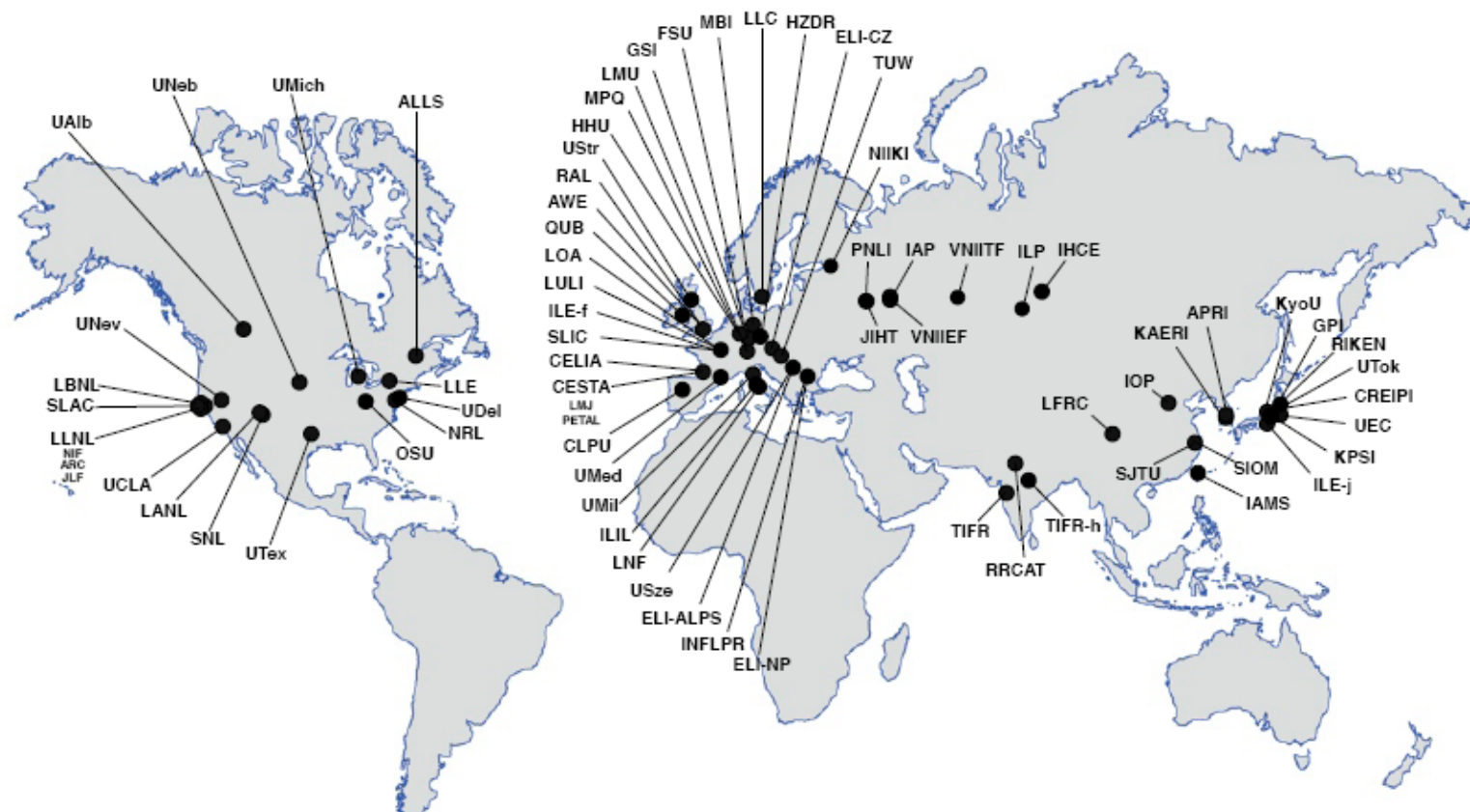
DPSS Laser Amplifiers



HIGH-INTENSITY LASERS: DIODE SPECIFICATIONS

High-Intensity Laser Overview

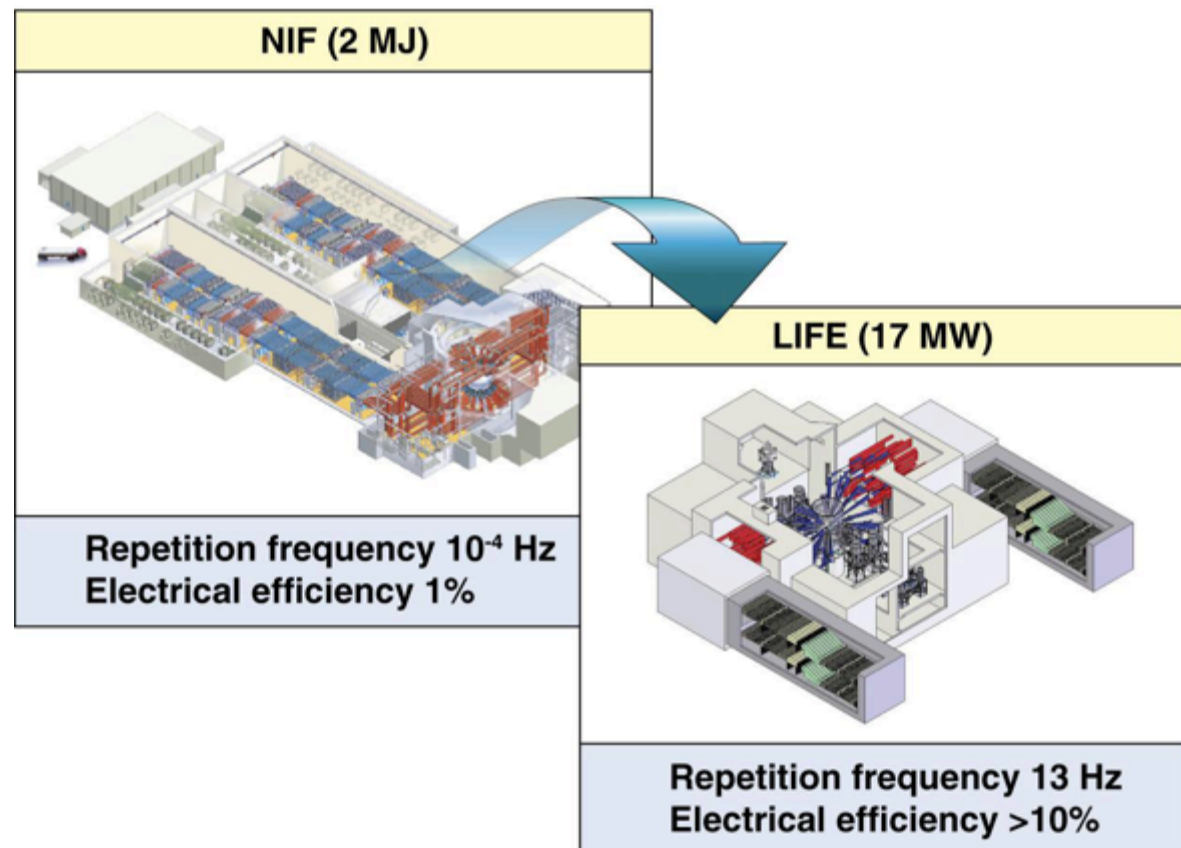
2010 ICUIL World Map of Ultrahigh Intensity Laser Capabilities



Dr. C.P.J. Barty – LLNL
Chief Technology Officer – NIF / Photon Science Directorate
International Community on Ultra-High Intensity Lasers

NIF → LIFE

- Lessons learned from NIF provide the framework for LIFE
- Many differences, including the transition from flashlamp pumping to diode pumping
- Diode costs currently represent 30-50% of the entire system cost



LIFE Diode Specifications (Technical)



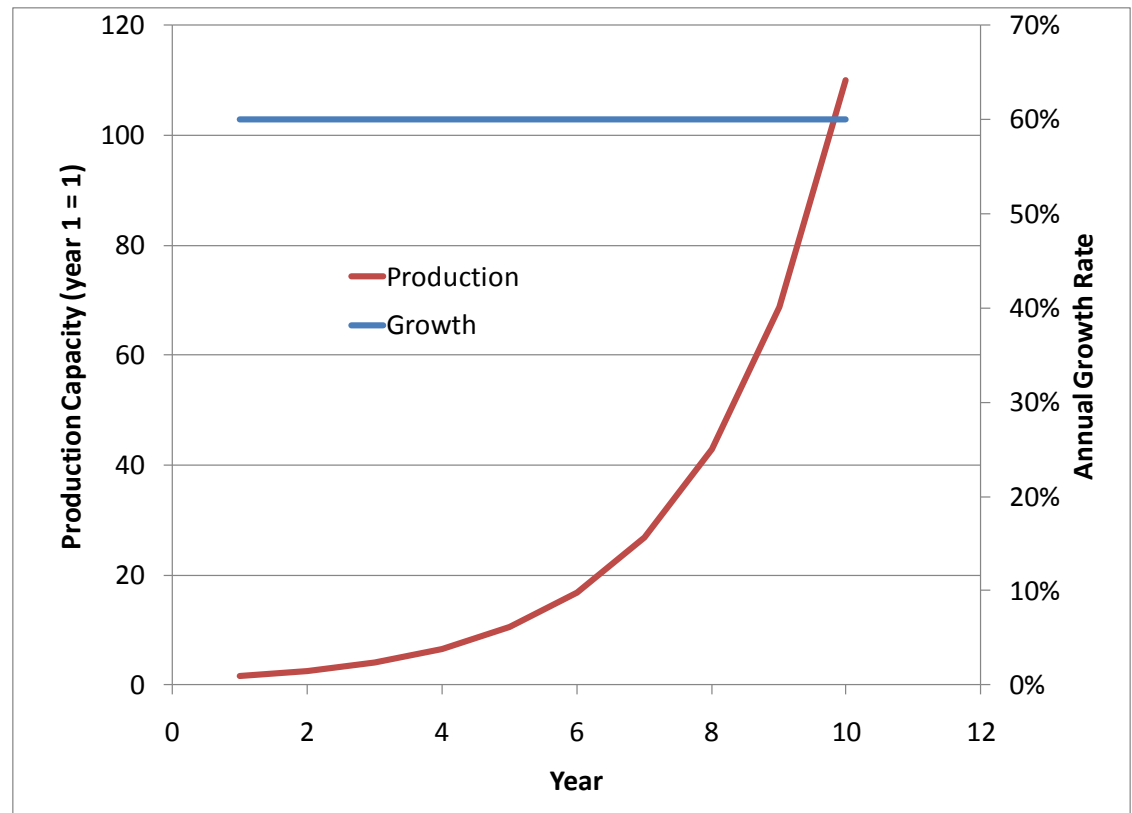
| Item | Units | Minimum Value | Target Value | Current State / Comments |
|-------------------------------|--------------------------------|---------------|--------------|--|
| Intensity | kW/cm ² | 10 | 25 | ~ 10 (300W @ 350 μm) ~ 22 (300W @ 150 μm) May require 600-700W bar |
| Efficiency | | 70% | 75% | 60-70% (commercial) 70+ (SHEDS, BRIOLAS) |
| Fast axis divergence | degrees FW 1/e ² | ±4 | ±3 | |
| Slow axis divergence | degrees FWHM | ±10 | ±7 | Matches divergence of typical unlensed bar |
| Wavelength | nm | | 872 | Typical structure |
| Wavelength spread | nm | ±8 | ±5 | |
| MTTF | Gshots | | 14 | Easily Achievable |
| Repetition Rate | Hz | | 15 | Low heat → Novel (low-cost) packaging |
| Pulse Width | μs | | 200 | “ |
| Duty Cycle | % | | < 0.5 | “ |
| Temperature of mounting plate | °C | | 5 | |
| Packaging Density | | | | Minimal dead space between diode bars – largest challenge |

Now The Hard Part...

- Order of Magnitude numbers:
- Total pump power 50-200 GW
 - ~ 200 million bars @ 500 W/bar
 - ~ 2 orders of magnitude higher than current supply
- Schedule ~ 8-10 years
 - Subject to congressional funding
- Price target ~ \$0.01 / W
 - Includes packaging and lensing
 - ~ 2 orders of magnitude cheaper than today
- **And this is just for the first plant...**

What is required?

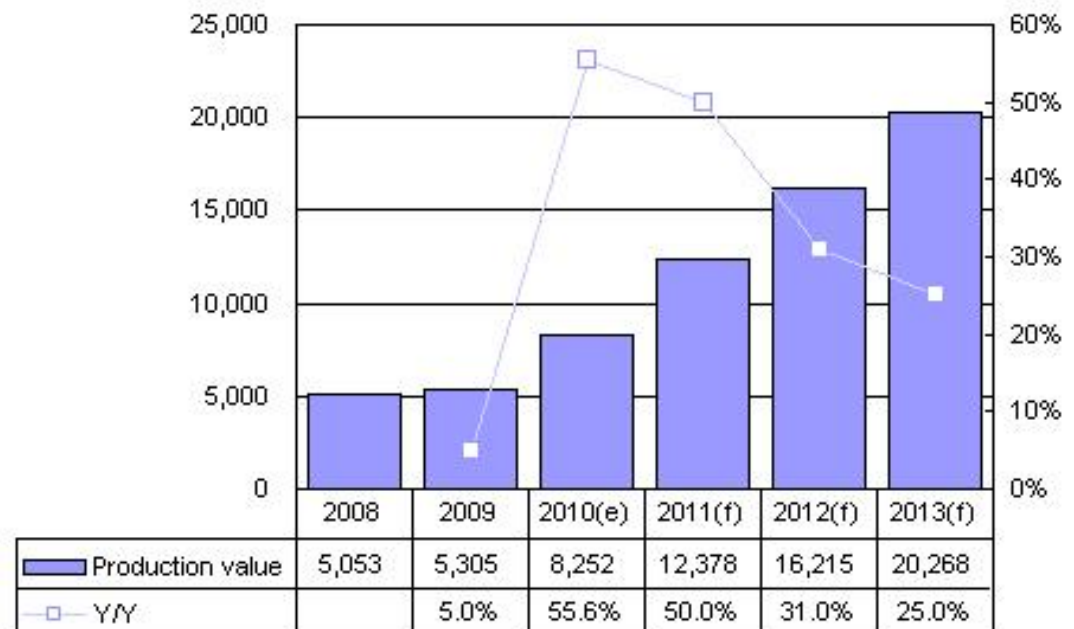
- Increasing supply capability by two orders of magnitude requires a \sim 60% AGR for 10 years
- In line with LED ramp-up
 - Much DOE involvement / investment
 - Significant Chinese government investment
- 8-year schedule \rightarrow 80% AGR
- *If we're going to do this, we need to get started*



LED Examples

- Tremendous increase in LED production
- MOCVD reactor shipments:
 - 2009: ~ 250
 - 2010: ~ 800
 - 2011: ~ 1100
- 50% year-over-year growth in the production value of high-brightness LEDs
- 300-400 reactors/year needed to meet demand
- Chinese subsidies have driven the market
- Lumens/\$ is ahead of industry-established roadmap
- Concerns:
 - Oversupply of reactors
 - Undersupply of MOCVD engineers

High-brightness LED market production value, 2008-2013 (US\$m)



Sources: DigiTimes
LEDs Magazine
DOE SSL Manufacturing Workshop

Different Thinking

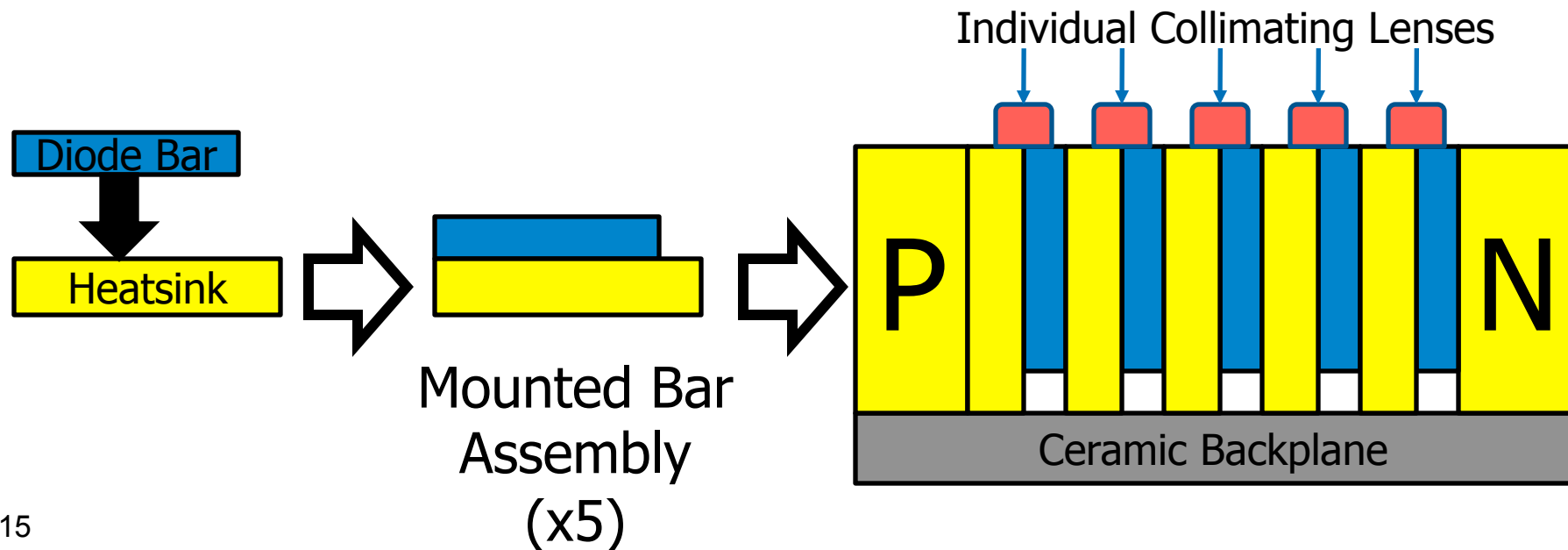


| 2012 | ~ 2022 |
|---|--|
| cm edge emitters | <ul style="list-style-type: none">• bigger edge emitters• VCSELs / wafer-level processing• not yet invented... |
| Conventional diode packaging | <ul style="list-style-type: none">• High density packaging• Wafer scale |
| Business driven by science | Business driven by manufacturing |
| Sequential iterations on existing manufacturing processes | Transition to more LED-like thinking |
| Current pace of market penetration | Increased market penetration due to lower costs |

What would the market look like if diode bars were essentially free?

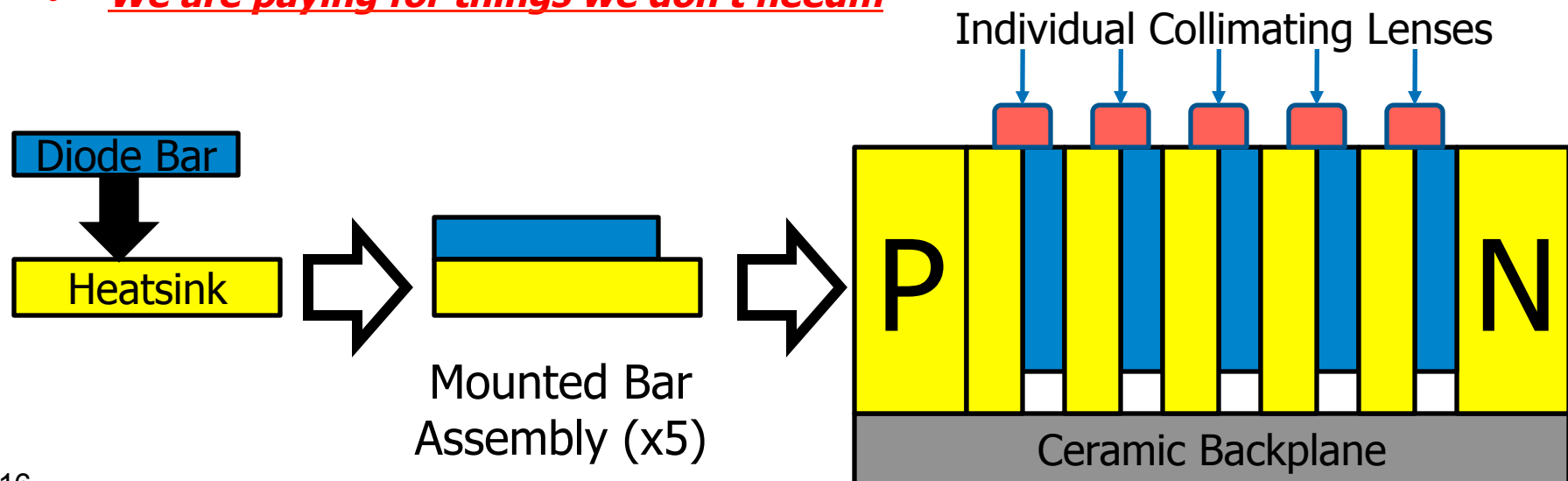
Conventional Diode Packaging

- Power density in a standard array defined by per-bar power and width of heatsink located between bars
- Heatsink cost \sim bar cost
- Lenses individually attached (manually or automatically)
- Even in automated processes, all bars treated as individuals
 - Bar cleaving / singulation
 - Facet coating
 - Packaging



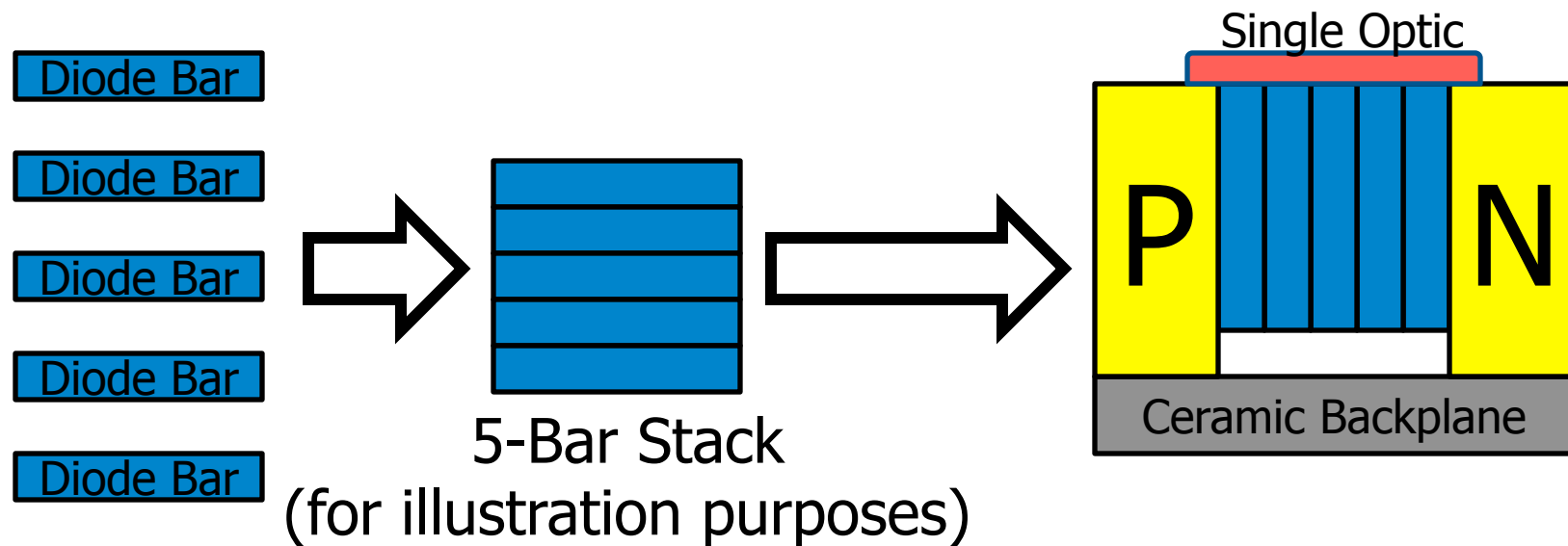
Why do we do this?

- Manufacturing methods developed to meet a wide variety of specifications
- Bars individually mounted to heatsink → Allows for heat dissipation at higher repetition rates (100s-1000s of Hz)
 - Connection to backplane
 - Space between heat sources
- Individual collimating lenses → Facilitates excellent collimation in the fast axis (< 0.15° FWHM)
- Neither of these are required for the current LIFE design, but the costs are still there
- **We are paying for things we don't need...**



High Density Stack Packaging

- Low duty cycle of fusion power plants allows for novel packaging
- Elimination of heatsinks reduces cost and increases intensity
- Single optic for stack, engineered to produce required fast-axis divergence
- Arrays can be produced in stack sizes of 20-50 bars
- Drastically increased power density



Array Comparison

- Difference in packaging & power density clearly seen in photograph and near field image
- NGCEO has been packaging HDS (and variants) for ~ 12 years
- Package is limited only by heatsinking
 - No heat sink between bars
 - ➔ Middle bars run at higher temperatures
 - No effect seen up to $\sim 2\%$ duty
- Only possible because of elimination of COD failure mode (elimination of collateral damage)

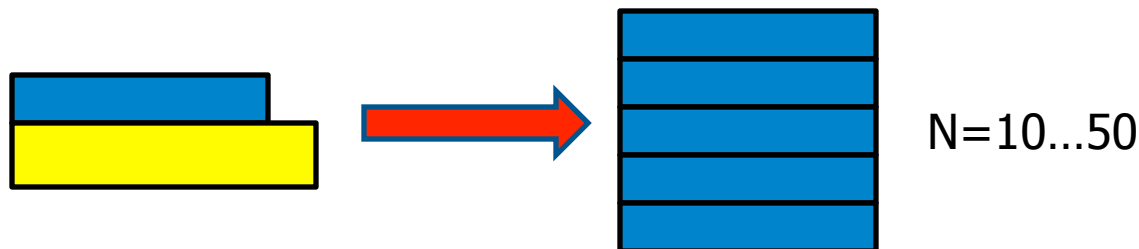
150 μm pitch

400 μm pitch



What does this buy us (cost)?

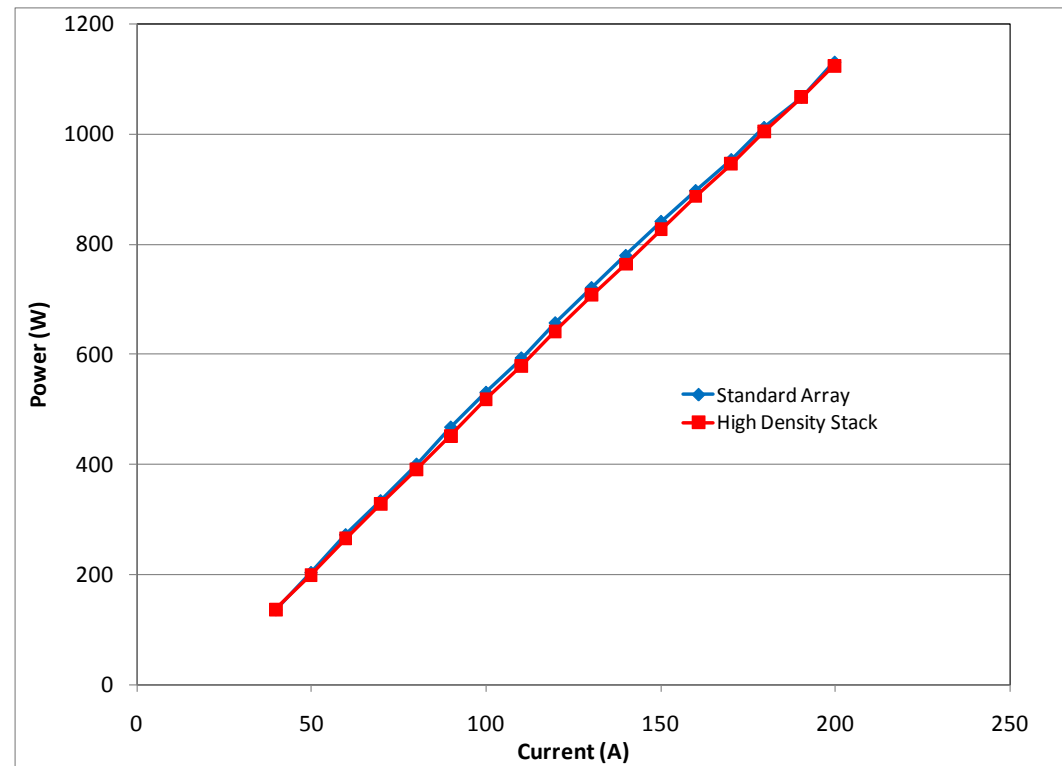
- Elimination of heatsink
 - Reduced material cost
 - Elimination of $\sim 50\%$ of solder bonds (alignment, cost)
- Changes the basic building block



- Changes processing options
- Build/test/etc. in “blocks” instead of single bars/assemblies

PI Data – High Density Stacks

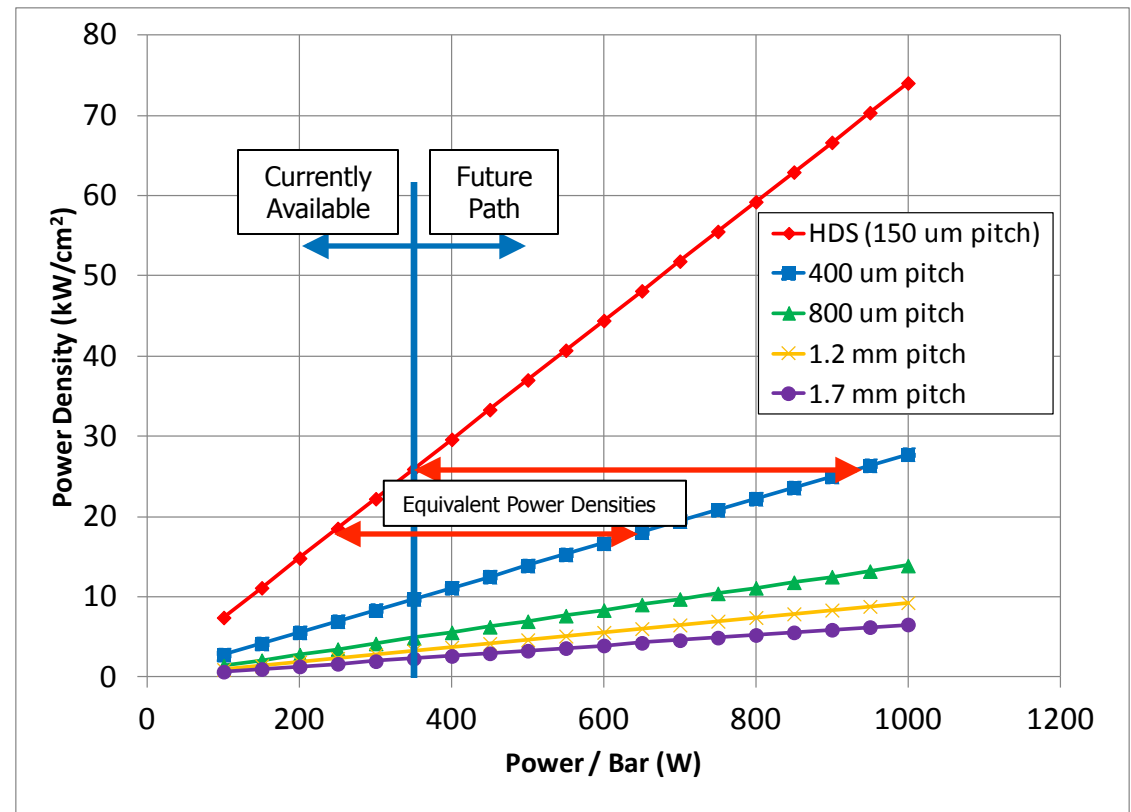
- PI data for standard and high density stacks shown at right
- 20 Hz, 150 μ s
 - Similar duty cycle to typical fusion installations
- No change in slope or threshold observed
- Other test data indicates this is the case up to $\sim 2\%$ duty cycle
- Additional optimization will increase operating envelope of this package



Power Density Comparison: High Density Stack vs. Standard Array



- High Density Stacks offer power densities not available with standard arrays
- HDS @ 150W/bar offers the same power density as 400 μm pitch array @ 400W/bar
- HDS available with same bars as standard arrays
 - Same peak power levels



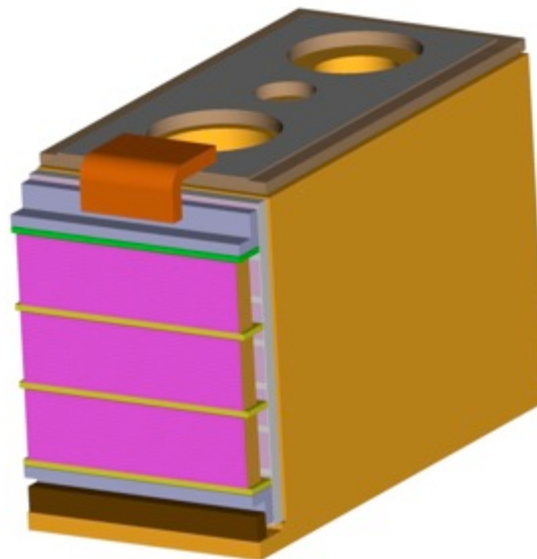
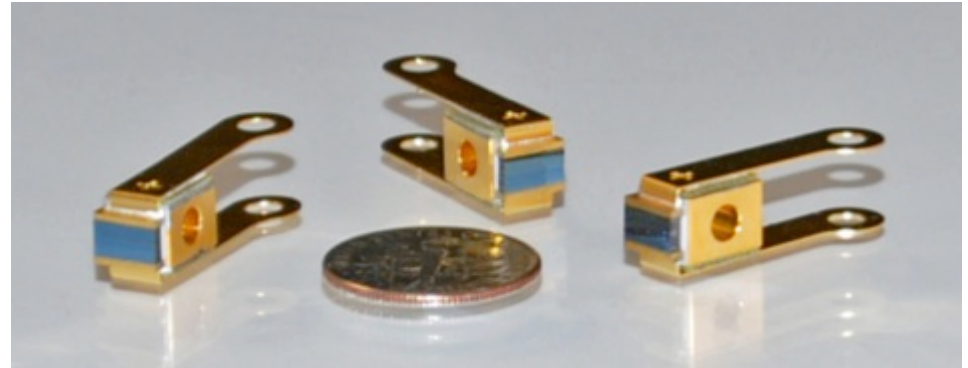
50-bar HDS @ 500 W/bar



| Specification | Specification | Example Package | Comment |
|-----------------------|--------------------------------|-----------------------|----------------------------------|
| Intensity | 25 kW/cm ² | 50 kW/cm ² | Higher intensities are available |
| Efficiency | 75% | 60+% | Higher efficiency available |
| Fast-axis divergence | ±3 degrees (1/e ²) | TBD | |
| MTTF | 14 billion shots | >> 14 billion shots | Higher lifetimes are available |
| Stack Power | | 25 kW | |
| # of stacks | | 400k | |
| # of bars | | 200 million | |
| Total price of diodes | | ??? | |

Further Examples

- HDS arrays based on mini-bars
- Segmented HDS arrays
 - 60 bars
 - Design for 15-25 arrays around a thick disk
 - $\sim 12\text{kW}$ in 1cm^2

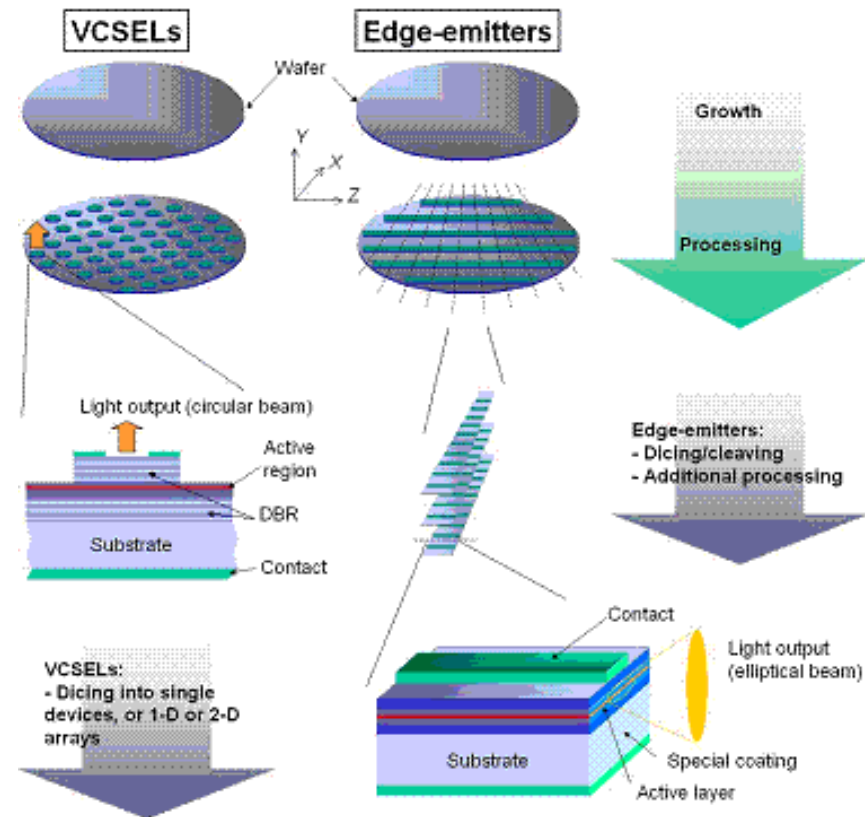


Other Challenges

- Every photon requires an electron
 - 500-700W bars → 500-700A drivers
- Diodes packed in close proximity
 - Small drivers located near the array, or
 - A power delivery and inductance nightmare
- Required for production installations
- Required for all diode manufacturers
 - Testing, burn-in, life test, etc.

What about VCSELs?

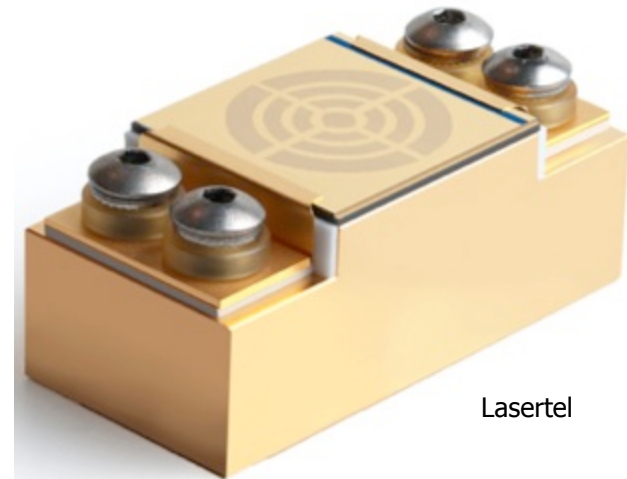
- Why VCSELs? – Long the “holy grail” of the semiconductor laser field
 - Low-divergence beam
 - Temperature insensitivity ($\sim 1/5^{\text{th}}$ typical edge emitter)
 - ➔ Simpler cooling requirements
 - ➔ Lower system cost
 - Narrow spectral linewidth
 - Wafer-level processing
 - ➔ Pathway to low device cost



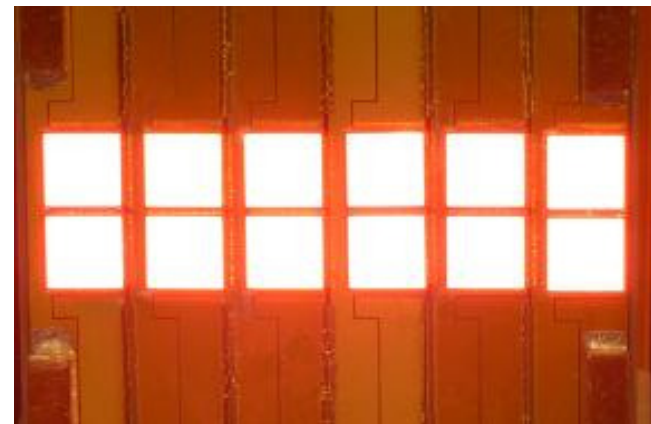
Princeton Optronics

Why not VCSELs?

- Insufficient power density
- Current product offerings:
 - Lasertel: 1kW in 1cm² (also 40% PCE)
 - Princeton Optronics: 1.2kW in >1cm² (35% PCE)
- Edge-emitters have a big head start:
 - > 1 order of magnitude in power density
 - 1.5-2x in PCE



Lasertel



~ 5.8mm x 20mm
Princeton Optronics

Conclusions



- The technical specifications of the LIFE project are directly achievable from today's technology
 - Can be surpassed in many cases
- The technical specs for the arrays may be the easiest part of the whole project, and they're not easy
- Will need LED-like increases in supply chain to make LIFE a reality
- The sooner we start, the sooner we will get there

NORTHROP GRUMMAN

